



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

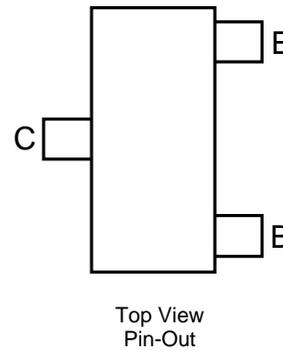
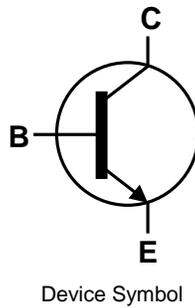
- $BV_{CEO} > 50V$
- $BV_{CEV} > 80V$ Forward Blocking Voltage
- $I_C = 5A$ high Continuous Collector Current
- $I_{CM} = 12A$ Peak Collector Current
- Low Saturation Voltage, $V_{CE(SAT)} < 40mV @ 1A$
- $R_{CE(SAT)} = 24m\Omega$ for a Low Equivalent On-Resistance
- Complementary PNP Type: NK-ZXTP2025F

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per
MIL-STD-202, Method 208 (A3)
- Weight 0.008 grams (Approximate)

Applications

- MOSFET and IGBT Gate Driving
- Motor Drive
- Relay Lamp and Solenoid Drive
- DC-DC Converters



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CEV}	80	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	5	A
Peak Pulse Current	I _{CM}	12	A
Base Current	I _B	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

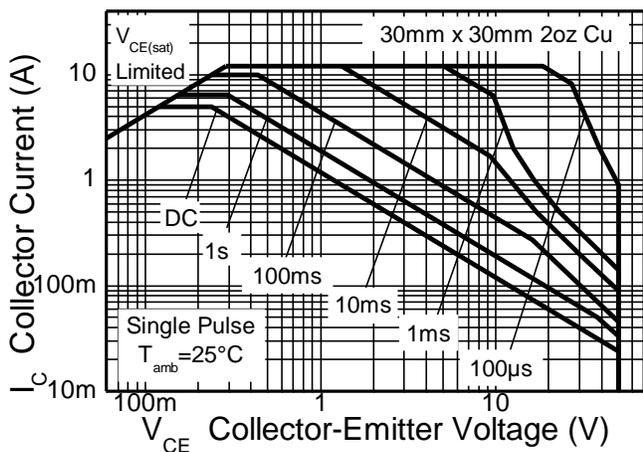
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	1.0	W
		8.0	
		1.2	
		9.6	
Thermal Resistance, Junction to Ambient	R _{θJA}	1.56	°C/W
		12.5	
		125	
Thermal Resistance, Junction to Lead	R _{θJL}	104	°C/W
		80	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

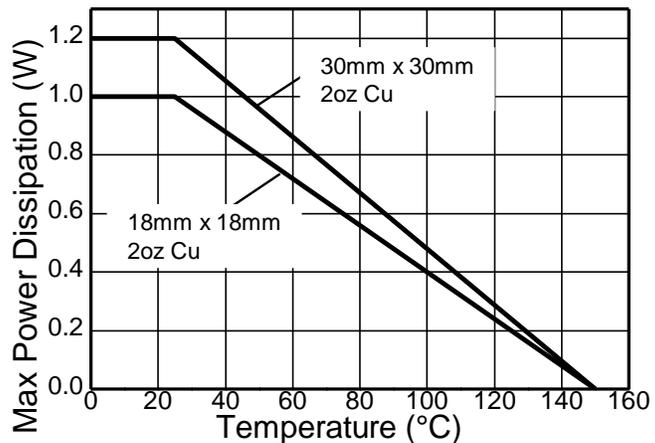
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 18mm x 18mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as note (5), except the device is mounted on 30mm x 30mm 2oz copper.
 7. Same as note (6), except measured at t < 5 seconds.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

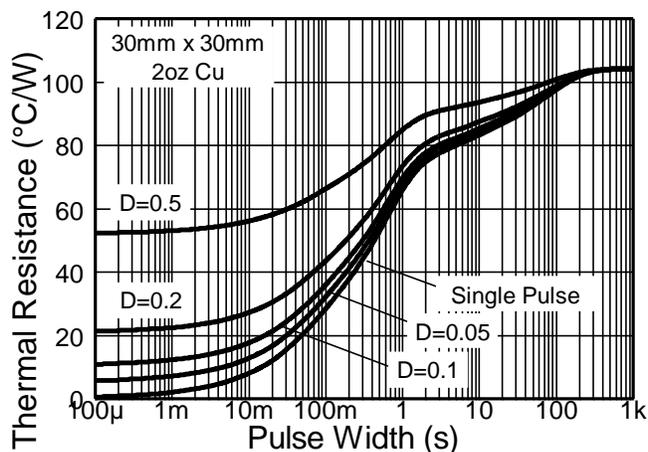
Thermal Characteristics and Derating information



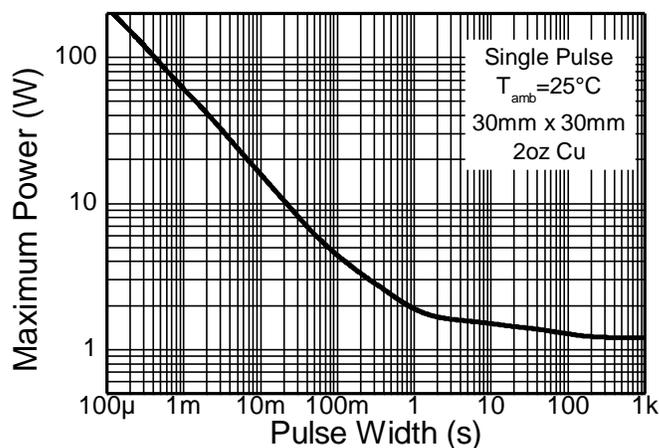
Safe Operating Area



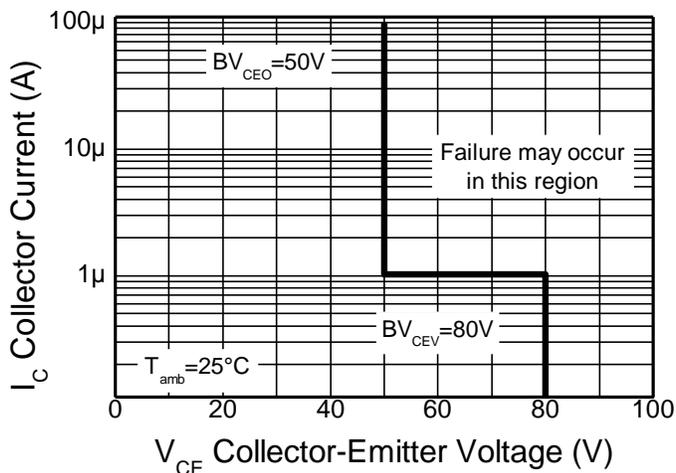
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



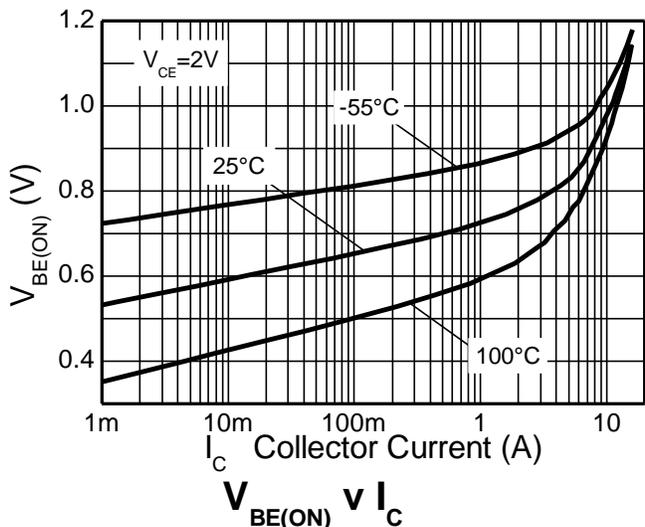
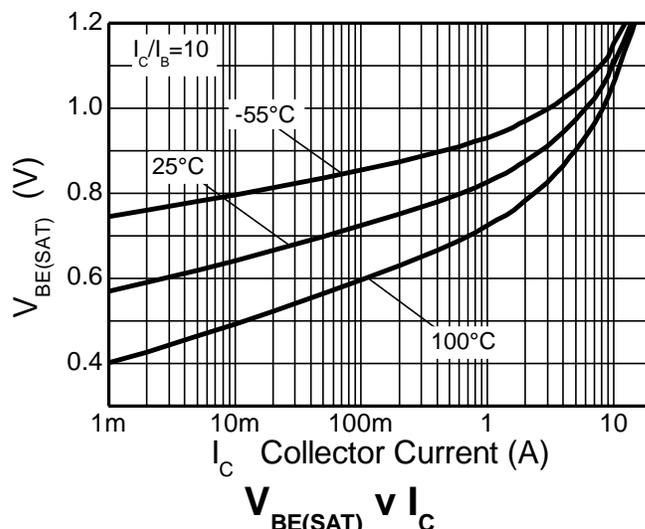
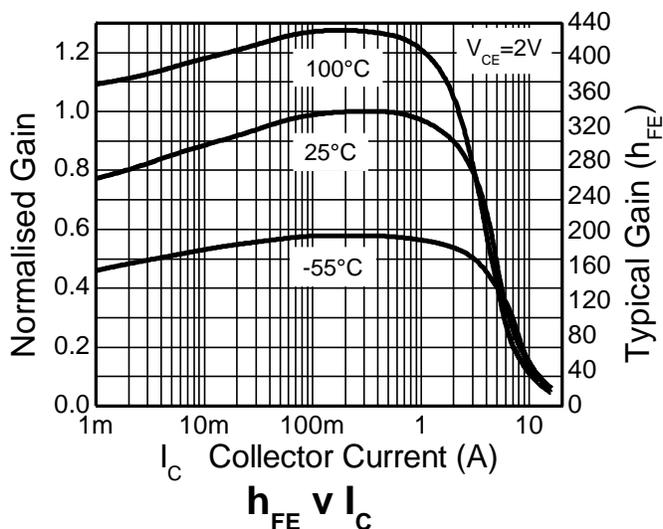
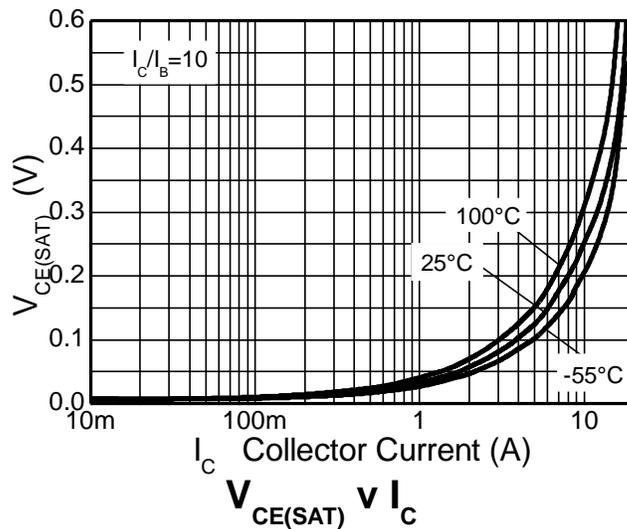
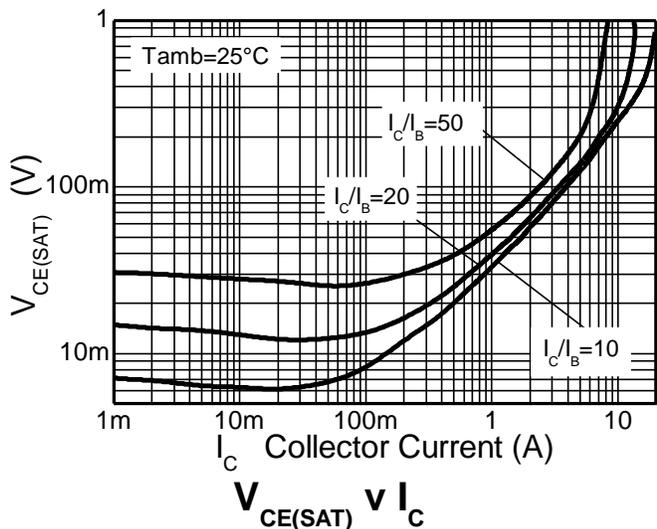
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

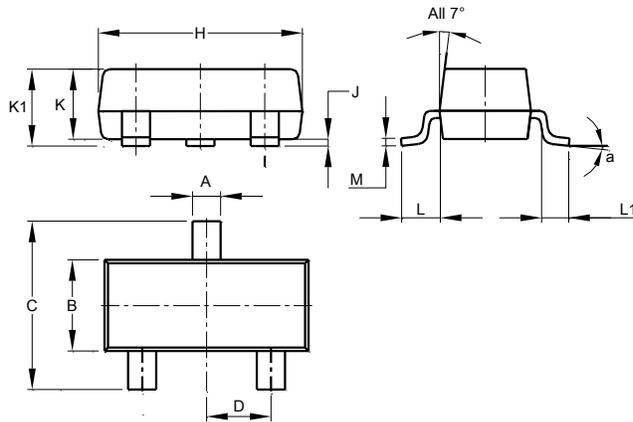
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	175	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	80	175	-	V	I _C = 1μA, -1V < V _{BE} < +0.3V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	50	75	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	-	V	I _E = 100μA
Collector – Emitter Cut-Off Current	I _{CEV}	-	<1	20	nA	V _{CE} = 60V, V _{BE} = -1V
Collector - Base Cut-Off Current	I _{CBO}	-	<1	20	nA	V _{CB} = 60V
Emitter Cut-off Current	I _{EBO}	-	<1	10	nA	V _{EB} = 6V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	190 200 200 80	300 350 340 125	- 560 - -	-	I _C = 10mA, V _{CE} = 2V I _C = 500mA, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 5A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	- - - -	13 30 80 135	18 40 110 170	mV	I _C = 100mA, I _B = 5mA I _C = 1A, I _B = 100mA I _C = 2A, I _B = 40mA I _C = 5A, I _B = 250mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	- -	800 920	900 1000	mV	I _C = 2A, I _B = 40mA I _C = 5A, I _B = 250mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	830	930	mV	I _C = 5A, V _{CE} = 2V
Transition Frequency	F _T	-	125	-	MHz	I _C = 500mA, V _{CE} = 10V, f = 50MHz
Output Capacitance	C _{obo}	-	29	-	pF	V _{CB} = 10V, f = 1MHz
Delay Time	t _(d)	-	16	-	ns	V _{CC} = 12V, I _C = 2.5A, I _{B1} = - I _{B1} = 125mA
Rise Time	t _(r)	-	27	-	ns	
Storage Time	t _(stg)	-	468	-	ns	
Fall Time	t _(f)	-	44	-	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

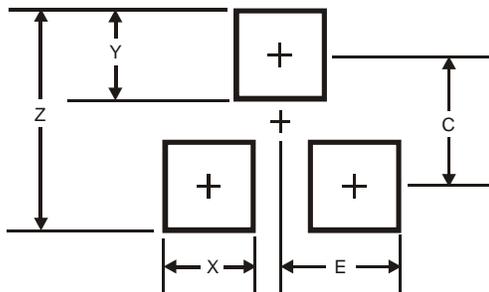


Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35